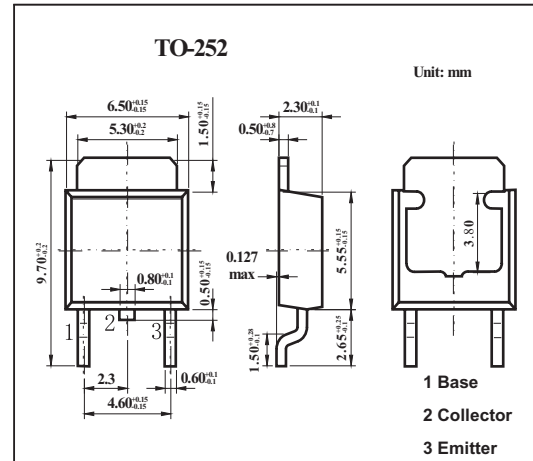


PNP Silicon Epitaxial Transistor

2SB962-Z

■ Features

- Low $V_{CE(sat)}$: $V_{CE(sat)} = -0.3V$.

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-40	V
Collector to emitter voltage	V_{CEO}	-30	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-3	A
Collector current pulse *	I_{CP}	-6	A
Total power dissipation	P_T	2	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature range	T_{stg}	-55 to +150	$^\circ C$

* $PW \leq 10ms$, duty cycle $\leq 50\%$.

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -30 V, I_E = 0$			-10	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -3.0 V, I_C = 0$			-1	μA
DC current gain *	h_{FE}	$V_{CE} = -2.0 V, I_C = -1A$	60	160	400	
		$V_{CE} = -2.0 V, I_C = -20mA$	30	150		
Collector saturation voltage *	$V_{CE(sat)}$	$I_C = -2A, I_B = -0.2A$		-0.3	-0.5	V
Base saturation voltage *	$V_{BE(sat)}$	$I_C = -2A, I_B = -0.2A$		-1	-2	V
Gain bandwidth product	f_T	$V_{CE} = -5.0 V, I_E = 100mA$		80		MHz
Output capacitance	C_{ob}	$V_{CB} = -10 V, I_E = 0, f = 1.0 MHz$		55		pF

* Pulsed: $PW \leq 350 \mu s$, duty cycle $\leq 2\%$

■ h_{FE} Classification

Rank	R	Q	P	E
h_{FE}	60~120	100~200	160~320	200~400